SH8K26

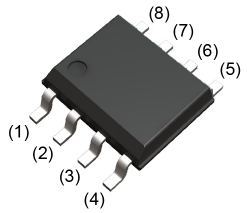
40V Nch+Nch Middle MOSFET

Datasheet

V_{DSS}	40V
$R_{DS(on)}$(Max.)	38mΩ
I_D	±6.0A
P_D	2.0W

●Outline

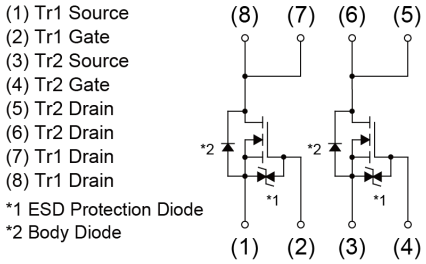
SOP8



●Features

1) Low on - resistance.
2) Small Surface Mount Package .
3) Pb-free lead plating ; RoHS compliant.
4) Halogen Free.

●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	2500
	Taping code	TB
	Marking	SH8K26

●Application

Switching

●Absolute maximum ratings (T_a = 25°C) <It is the same ratings for the Tr1 and Tr2>

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	40	V
Continuous drain current		I_D *1	±6.0	A
Pulsed drain current		$I_{D,\ pulse}$ *2	±12	A
Gate - Source voltage		V_{GSS}	±12	V
Avalanche energy, single pulse		E_{AS} *3	1.08	mJ
Avalanche current		I_{AS} *3	12	A
Power dissipation	total	P_D *4	2.0	W
	element	P_D *4	1.4	
Junction temperature		T_j	150	℃
Range of storage temperature		T_{stg}	-55 to +150	℃

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA} *4	-	89.3	-	

●Electrical characteristics (T_a = 25°C) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	40	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	27.3	-	mV/℃
Zero gate voltage drain current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V	-	-	1	μA
Gate - Source leakage current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±12V	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = 10V, I_D = 1mA	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	-4.6	-	mV/℃
Static drain - source on - state resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 6.0A	-	27	38	mΩ
		V_{GS} = 4.5V, I_D = 6.0A	-	35	50	
Transconductance	g_{fs}	V_{DS} = 10V, I_D = 6.0A	2.0	-	-	S

*1 Limited only by maximum temperature allowed.

*2 Pw ≤ 10μs, Duty cycle ≤ 1%

*3 L ≃ 10μH, V_{DD} = 20V, R_G = 25Ω, STARTING T_{ch} = 25℃ Fig.3-1,3-2

*4 MOUNTED ON A CERAMIC BOARD

*5 Pulsed

●**Electrical characteristics** (T_a = 25°C) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	280	-	pF
Output capacitance	C_{oss}	V_{DS} = 10V	-	105	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	30	-	
Turn - on delay time	$t_{d(on)}$ *5	V_{DD} ≃ 20V, V_{GS} = 10V	-	8	-	ns
Rise time	t_r *5	I_D = 3.0A	-	15	-	
Turn - off delay time	$t_{d(off)}$ *5	R_L = 6.5Ω	-	20	-	
Fall time	t_f *5	R_G = 10Ω	-	3	-	

●**Gate charge characteristics** (T_a = 25°C) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g *5	V_{DD} ≃ 20V, I_D = 6.0A V_{GS} = 5.0V	-	2.9	-	nC
Gate - Source charge	Q_{gs} *5		-	1.4	-	
Gate - Drain charge	Q_{gd} *5		-	0.6	-	

●**Body diode electrical characteristics** (Source-Drain) (T_a = 25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S *1	T_a = 25°C	-	-	1.6	A
Body diode pulse current	I_{SP} *2		-	-	12	
Forward voltage	V_{SD}	V_{GS} = 0V, I_S = 6.0A	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

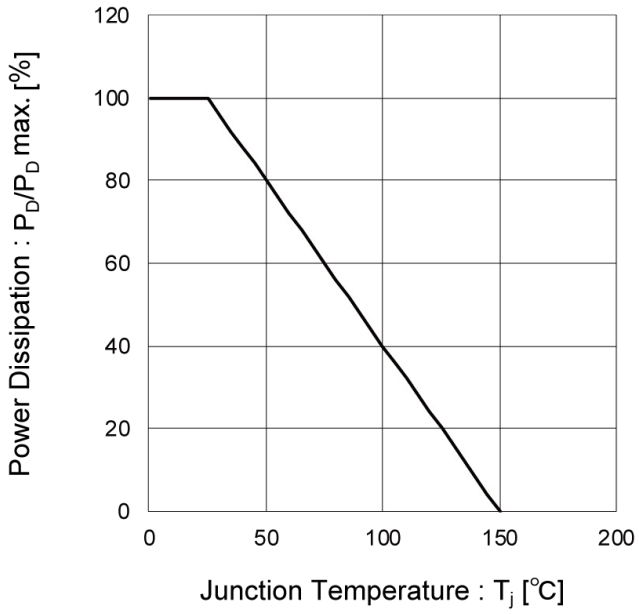


Fig.2 Maximum Safe Operating Area

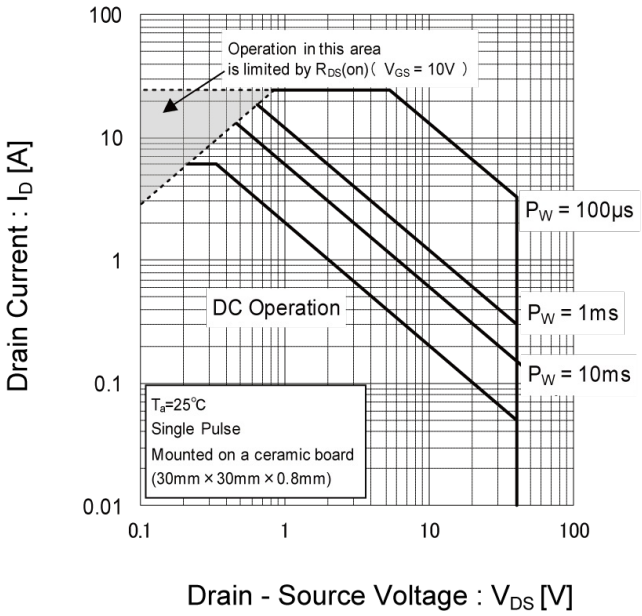


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

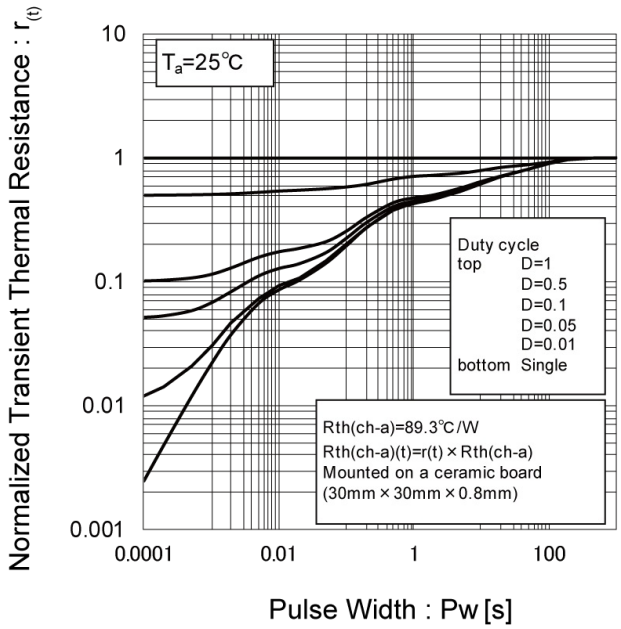
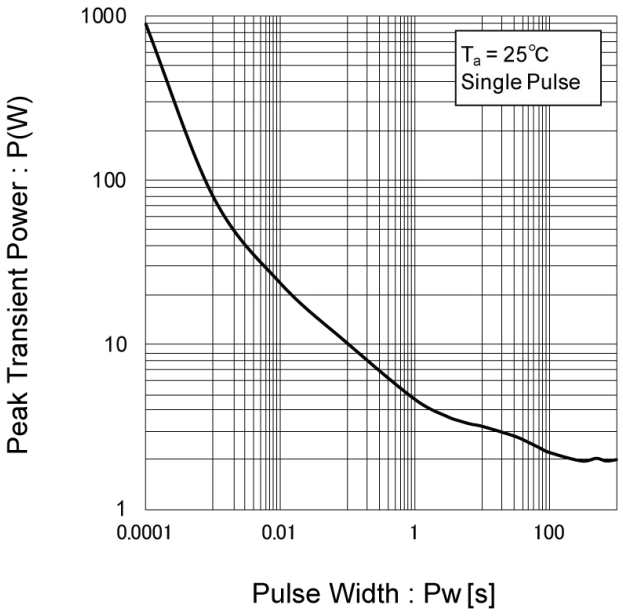


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

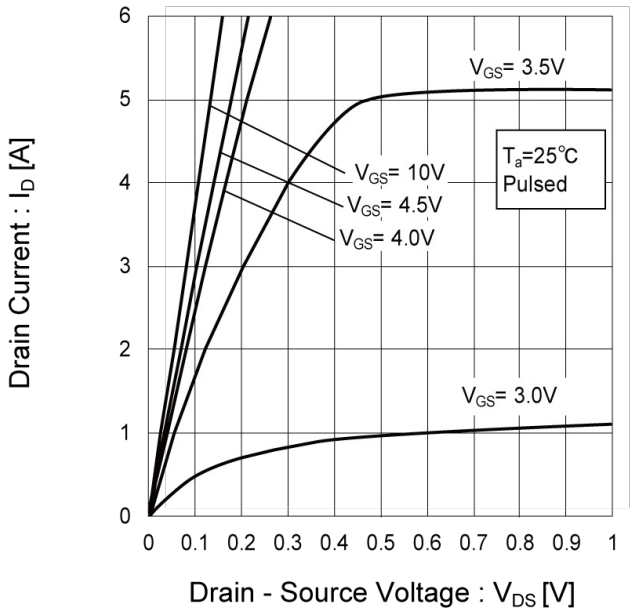


Fig.6 Typical Output Characteristics(II)

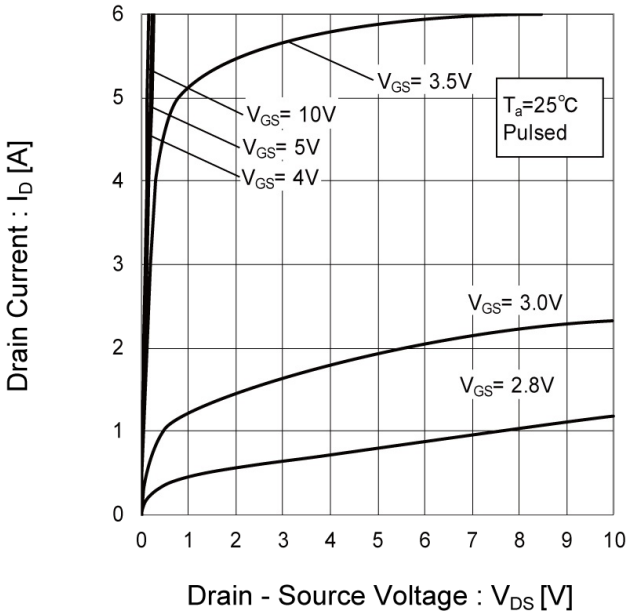
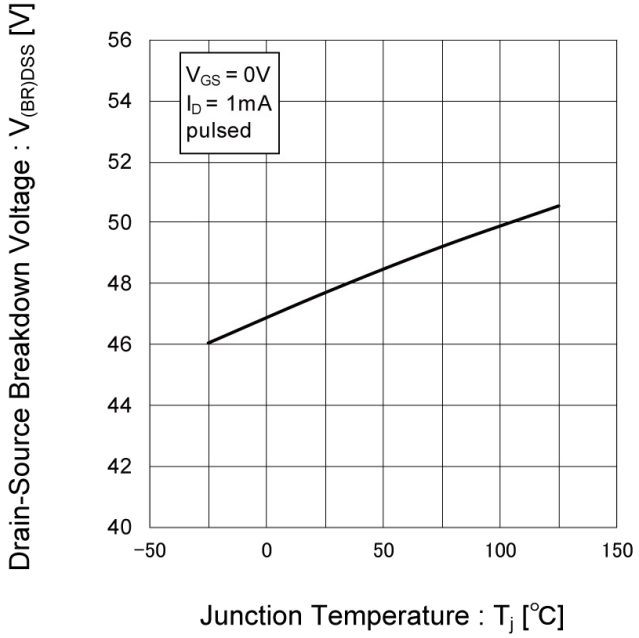


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

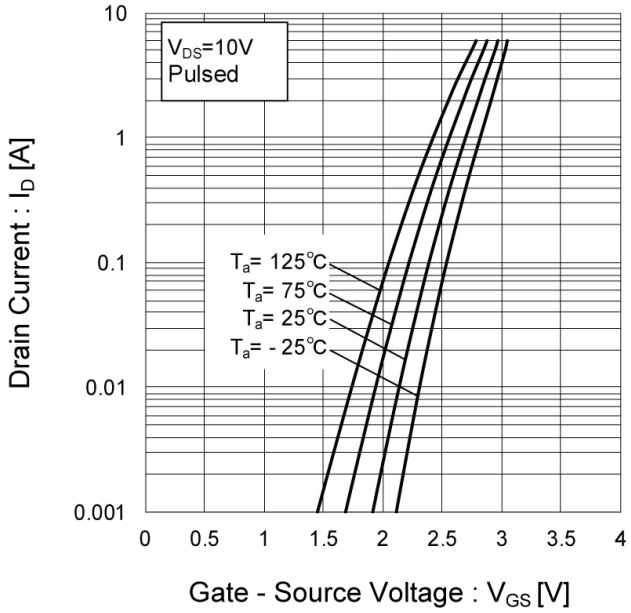


Fig.9 Gate Threshold Voltage vs. Junction Temperature

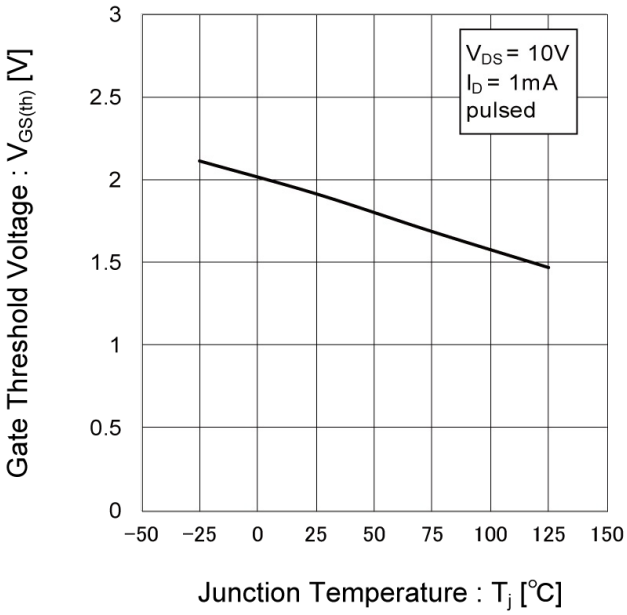
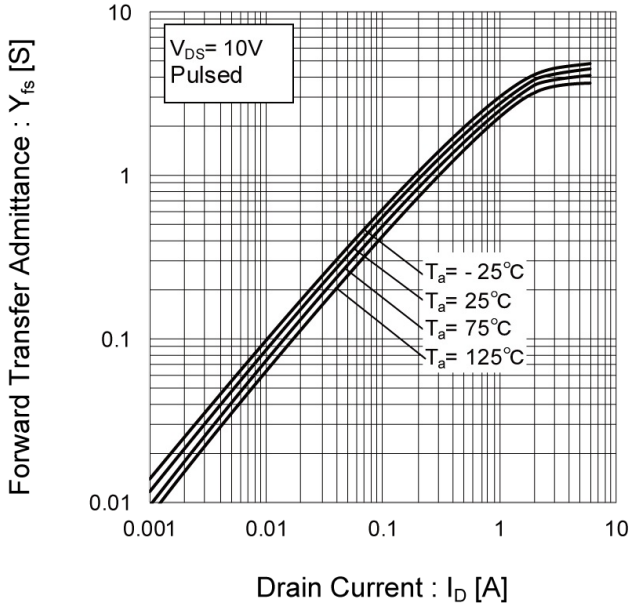


Fig.10 Tranceconductance vs. Drain Current



●Electrical characteristic curves

Fig.11 Drain Current Derating Curve

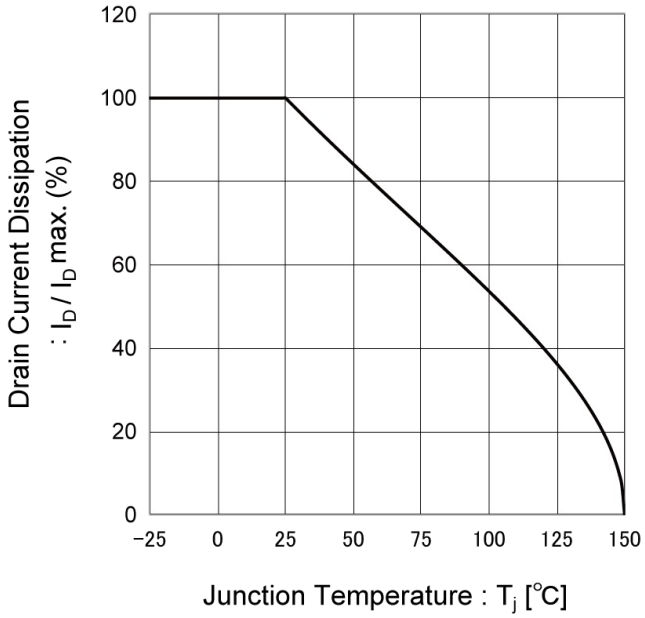


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

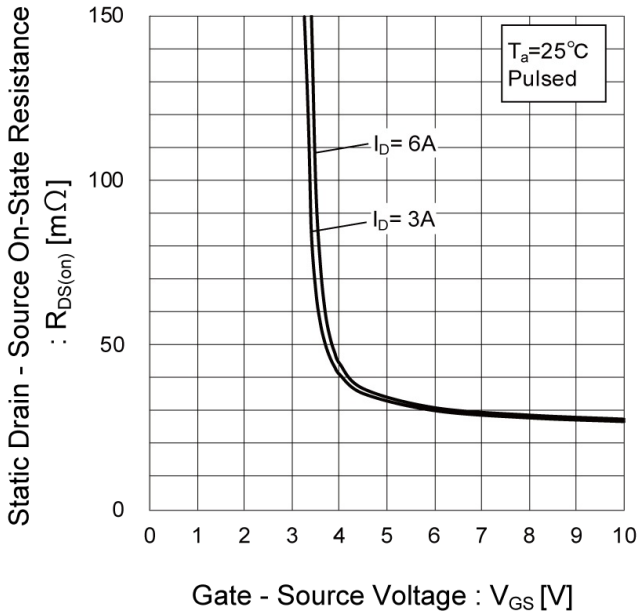
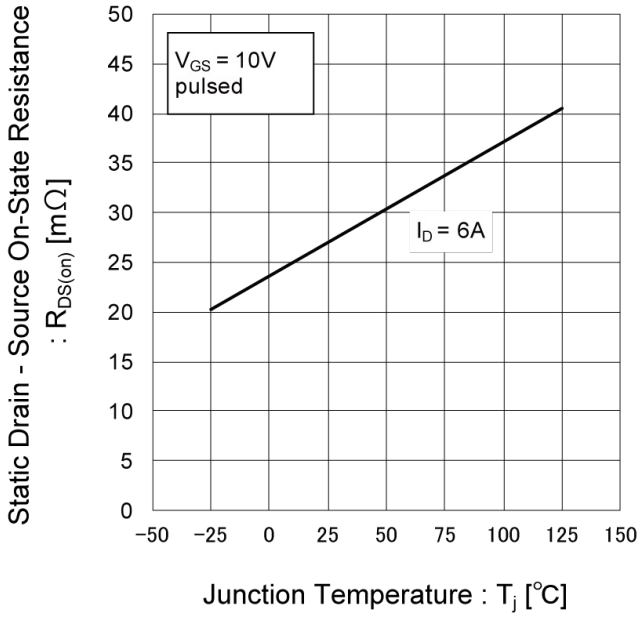


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

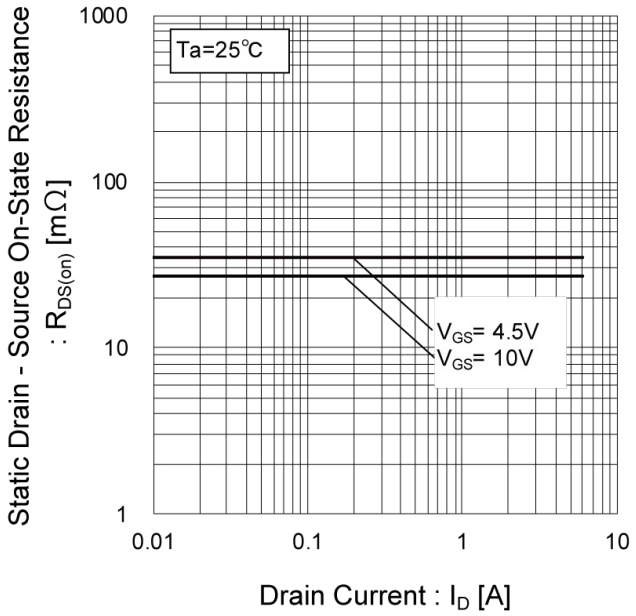


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

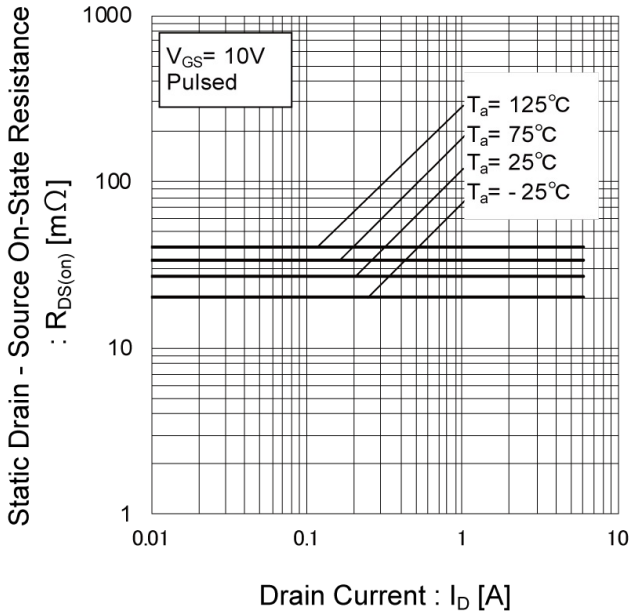
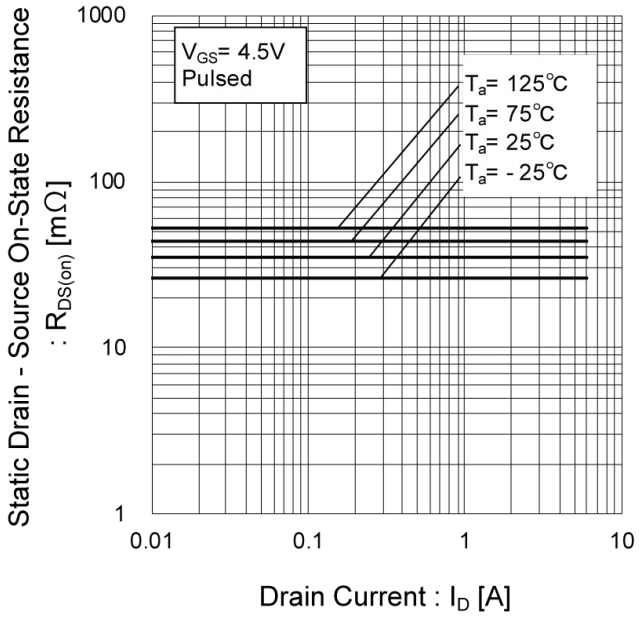


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

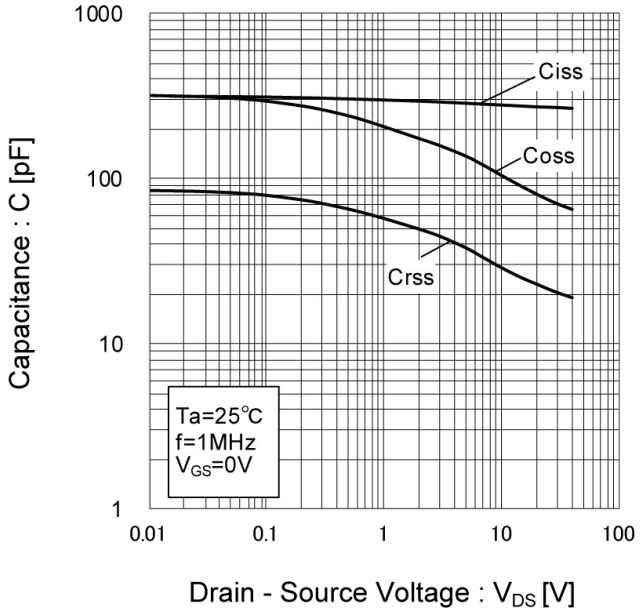


Fig.18 Switching Characteristics

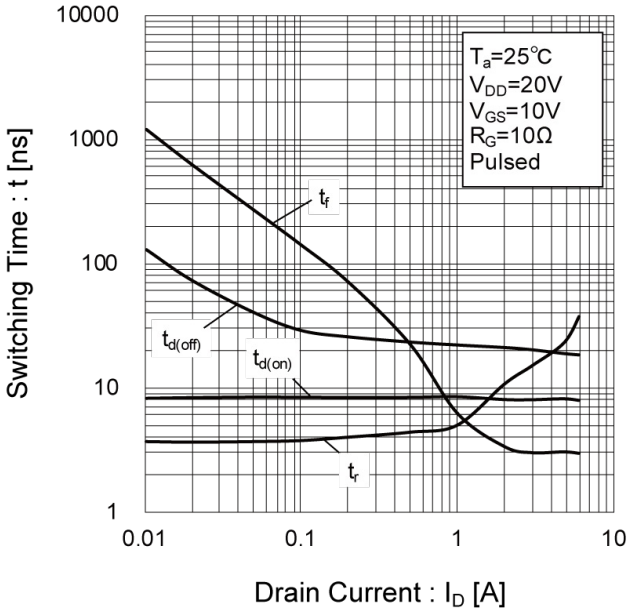


Fig.19 Dynamic Input Characteristics

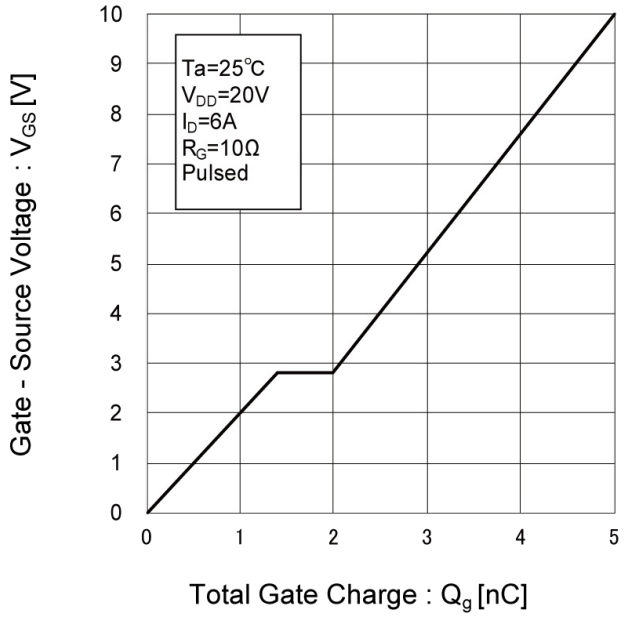
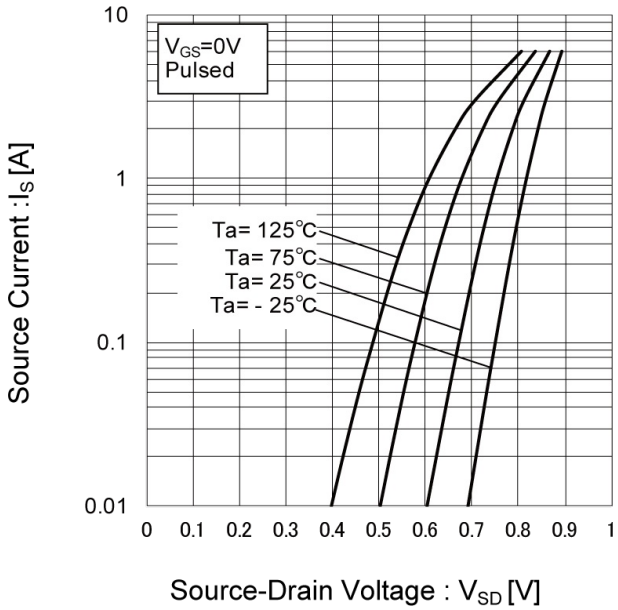


Fig.20 Source Current vs. Source Drain Voltage



●Measurement circuits <It is the same for the Tr1 and Tr2>

Fig.1-1 Switching Time Measurement Circuit

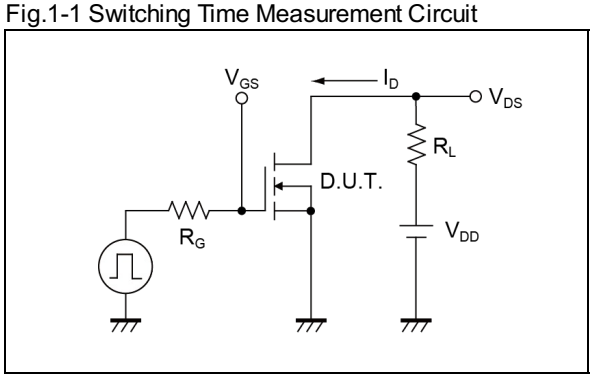


Fig.1-2 Switching Waveforms

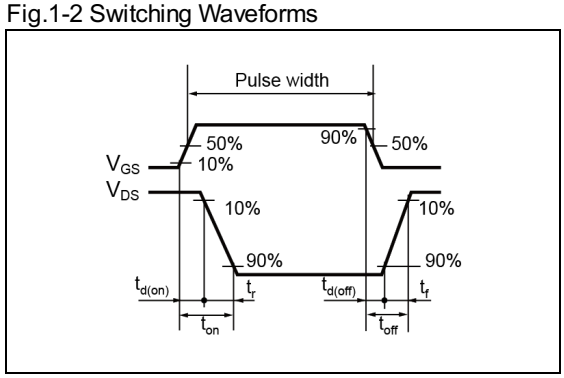


Fig.2-1 Gate Charge Measurement Circuit

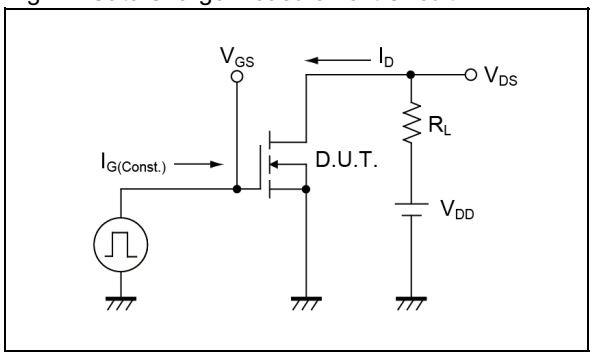


Fig.2-2 Gate Charge Waveform

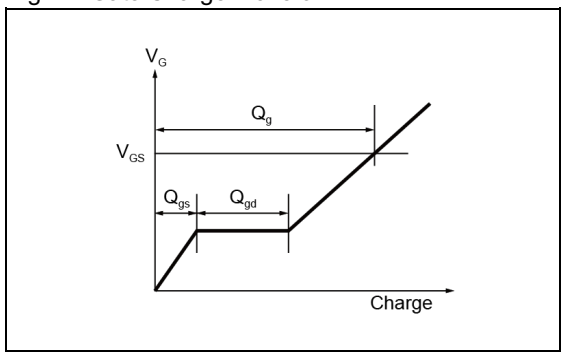


Fig.3-1 Avalanche Measurement Circuit

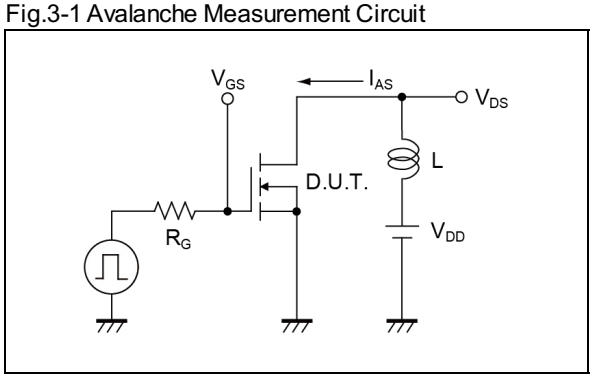
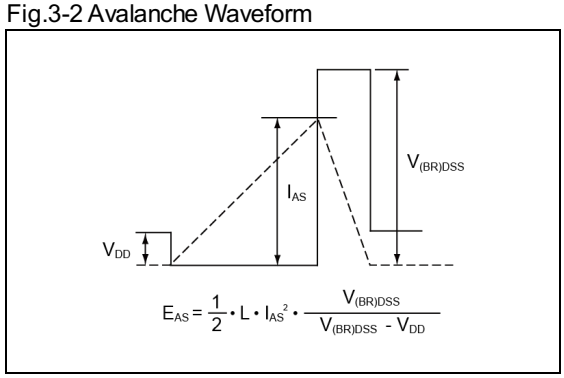
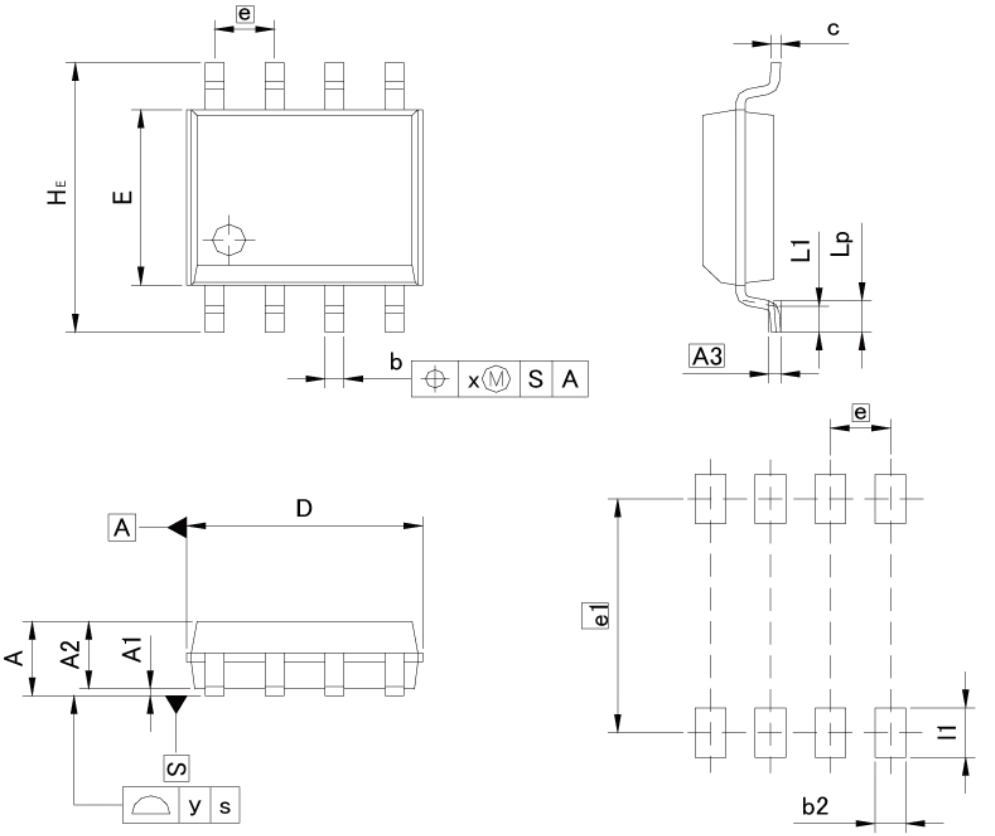


Fig.3-2 Avalanche Waveform



●Dimensions

SOP8



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	–	1.75	–	0.069
A1	0.15		0.006	
A2	1.40	1.60	0.055	0.063
A3	0.25		0.010	
b	0.30	0.50	0.012	0.020
c	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
e	1.27		0.050	
HE	5.70	6.30	0.224	0.248
L1	0.50	0.70	0.020	0.028
Lp	0.65	0.85	0.026	0.033
x	0.15		0.006	
y	0.10		0.004	

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	–	0.65	–	0.026
e1	5.15		0.203	
l1	–	1.15	–	0.045

Dimension in mm/inches

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

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7) The Products specified in this document are not designed to be radiation tolerant.

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ROHM SEMICONDUCTOR

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SH8K26 - Web Page

Part Number	SH8K26
Package	SOP8
Unit Quantity	2500
Minimum Package Quantity	2500
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes